

N-channel 80 V, 3.3 mΩ standard level MOSFET in TO-220

Rev. 1 — 27 October 2011

Product data sheet

#### **Product profile** 1.

#### 1.1 General description

Standard level N-channel MOSFET in TO-220 package qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive

#### 1.3 Applications

- DC-to-DC converters
- Load switch

- Motor control
- Server power supplies

#### 1.4 Quick reference data

Table 1.	Quick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	80	V
I <sub>D</sub>	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{10000000000000000000000000000000000$	[1]	-	-	120	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	338	W
Tj	junction temperature			-55	-	175	°C
Static cha	aracteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 100 °C; see Figure 12		-	4.6	5.4	mΩ
		$V_{GS}$ = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see <u>Figure 13</u>	[2]	-	2.8	3.3	mΩ
Dynamic	characteristics						
Q <sub>GD</sub>	gate-drain charge	$V_{GS} = 10 \text{ V}; \text{ I}_{D} = 75 \text{ A}; \text{ V}_{DS} = 40 \text{ V};$		-	27	-	nC
Q <sub>G(tot)</sub>	total gate charge	see Figure 14; see Figure 15		-	139	-	nC
	e ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 120 A; $V_{sup}$ ≤ 80 V; $R_{GS}$ = 50 Ω; unclamped		-	-	676	mJ

[1] Continuous current is limited by package.

[2] Measured 3 mm from package.

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#### N-channel 80 V, 3.3 m $\Omega$ standard level MOSFET in TO-220

### 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	
3	S	source	r O S	
mb	D	drain		mbb076 S
			SOT78 (TO-220AB)	

### 3. Ordering information

#### Table 3.Ordering information

Type number	Package		
	Name	Description	Version
PSMN3R3-80PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

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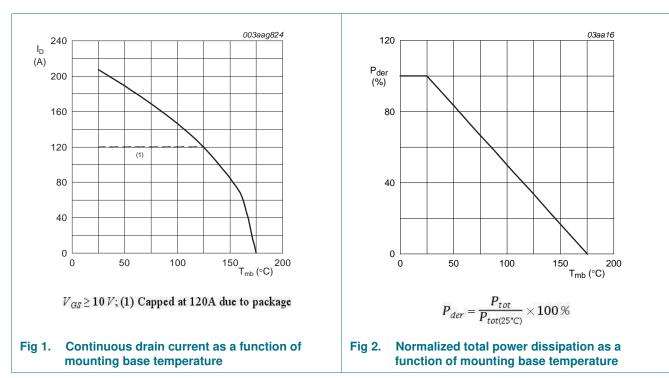
### 4. Limiting values

#### Table 4. Limiting values

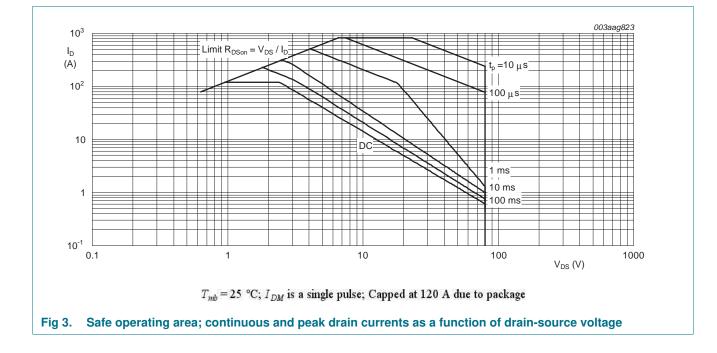
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	80	V
V <sub>DGR</sub>	drain-gate voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C; R <sub>GS</sub> = 20 kΩ		-	80	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	$V_{GS}$ = 10 V; $T_{mb}$ = 100 °C; see <u>Figure 1</u>	[1]	-	120	А
		$V_{GS}$ = 10 V; $T_{mb}$ = 25 °C; see <u>Figure 1</u>	[1]	-	120	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; see Figure 3		-	830	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	338	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-drai	n diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	120	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	830	А
Avalanche r	uggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$ \begin{array}{l} V_{GS} = 10 \text{ V};  \text{T}_{j(\text{init})} = 25 \text{ °C};  \text{I}_{\text{D}} = 120 \text{ A}; \\ V_{\text{sup}} \leq 80 \text{ V};  \text{R}_{\text{GS}} = 50  \Omega; \text{ unclamped} \end{array} $		-	676	mJ

[1] Continuous current is limited by package.



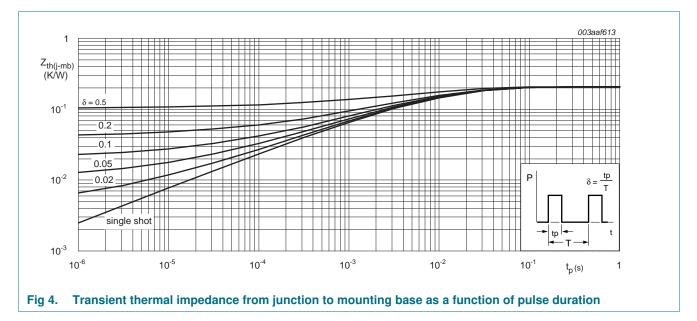
### PSMN3R3-80PS



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### 5. Thermal characteristics

Table 5.	mermai characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	see Figure 4	-	0.22	0.44	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	Vertical in free air	-	60	-	K/W



# Table 5 Thermal characteristics

#### N-channel 80 V, 3.3 m $\Omega$ standard level MOSFET in TO-220

### 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ\text{C}$	73	-	-	V
	voltage	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$	80	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see <u>Figure 10</u>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 10</u>	-	-	4.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u>	2	3	4	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 80 \text{ V};  V_{GS} = 0 \text{ V};  T_j = 25 ^{\circ}\text{C}$	-	0.02	10	μA
		$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	100	nA
		$V_{GS} = 20 \text{ V};  V_{DS} = 0 \text{ V};  T_j = 25 ^{\circ}\text{C}$	-	-	100	nA
$R_{DSon}$	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; see <u>Figure 12</u>	-	6.7	7.9	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 100 °C; see <u>Figure 12</u>	-	4.6	5.4	mΩ
		$V_{GS}$ = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; [1] see <u>Figure 13</u>	1 -	2.8	3.3	mΩ
R <sub>G</sub>	internal gate resistance (AC)	f = 1 MHz	-	0.9	-	Ω
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_{D} = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	135	-	nC
		$I_D = 75 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$	-	139	-	nC
Q <sub>GS</sub>	gate-source charge	see <u>Figure 14;</u> see <u>Figure 15</u>	-	51	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge		-	30	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	21	-	nC
Q <sub>GD</sub>	gate-drain charge		-	27	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V};$ see <u>Figure 14;</u> see <u>Figure 15</u>	-	5.8	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	9961	-	pF
C <sub>oss</sub>	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 16}{16}$	-	847	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	401	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 40 \text{ V}; \text{ R}_{L} = 0.53 \Omega;$	-	41	-	ns
t <sub>r</sub>	rise time	$V_{GS}$ = 10 V; $R_{G(ext)}$ = 10 $\Omega$ ; $I_D$ = 75 A	-	43	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	109	-	ns
t <sub>f</sub>	fall time		-	44	-	ns

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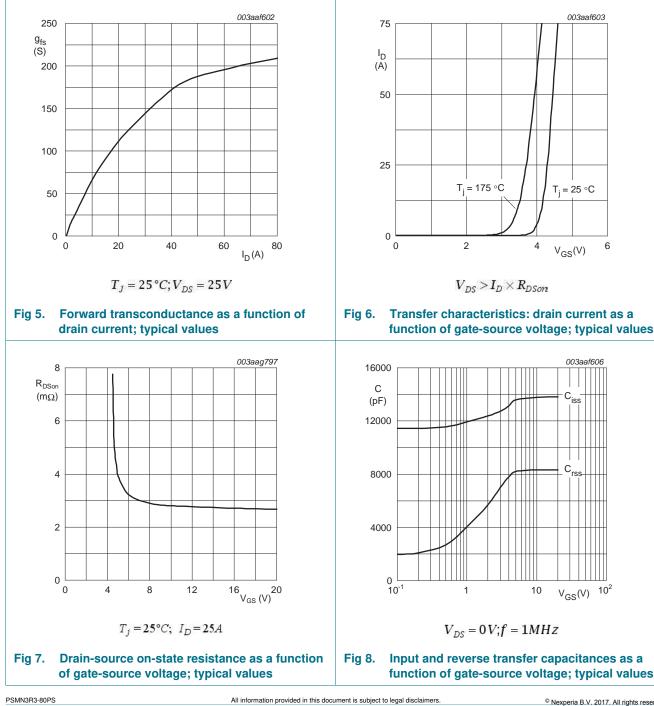
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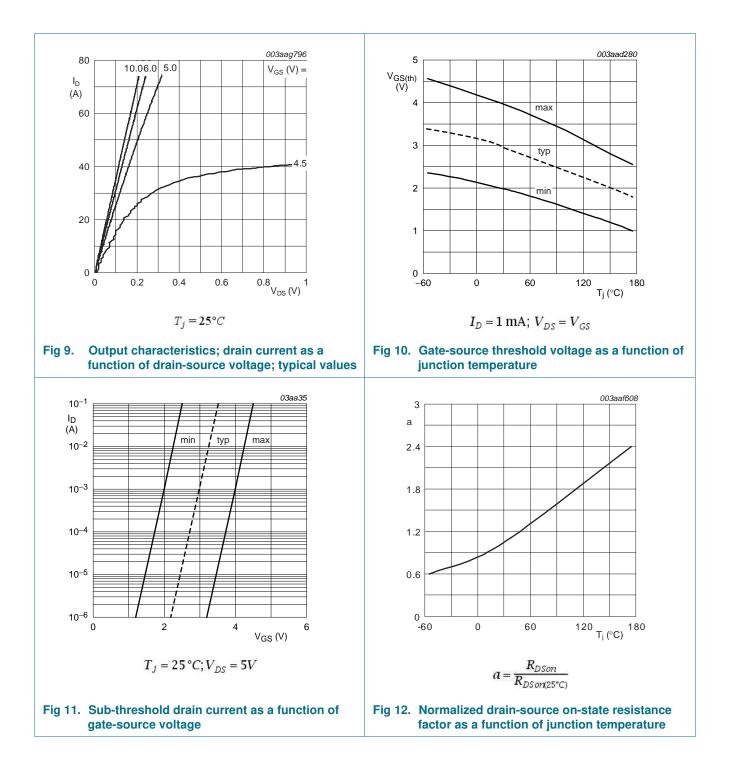
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Characteristics continued					
Parameter	Conditions	Min	Тур	Max	Unit
rain diode					
source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; see <u>Figure 17</u>	-	0.8	1.2	V
reverse recovery time	$I_{S} = 25 \text{ A}; \text{ d}I_{S}/\text{d}t = 100 \text{ A}/\mu\text{s};$	-	63	-	ns
recovered charge	$V_{GS} = 0 V; V_{DS} = 20 V$	-	121	-	nC
	Parameter rain diode source-drain voltage reverse recovery time	ParameterConditionsrain diodesource-drain voltage $I_S = 25 A; V_{GS} = 0 V; T_j = 25 °C;$ see Figure 17reverse recovery time $I_S = 25 A; dI_S/dt = 100 A/\mu s;$ $V_{GS} = 0 V; V_{GS} = 20 V$	rain diodesource-drain voltage $I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ reverse recovery time $I_S = 25 \text{ A}; \text{ d}I_S/\text{d}t = 100 \text{ A}/\mu s;$ $V_{CS} = 0 \text{ V}; V_{CS} = 20 \text{ V}$	ParameterConditionsMinTyprain diodesource-drain voltage $I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ -0.8reverse recovery time $I_S = 25 \text{ A}; dI_S/dt = 100 \text{ A}/\mu\text{s};$ -63	ParameterConditionsMinTypMaxrain diodesource-drain voltage $I_S = 25 A; V_{GS} = 0 V; T_j = 25 °C;$ see Figure 17-0.81.2reverse recovery time $I_S = 25 A; dI_S/dt = 100 A/\mus;$ $V_{GS} = 0 V'; V_{GS} = 20 V$ -63-

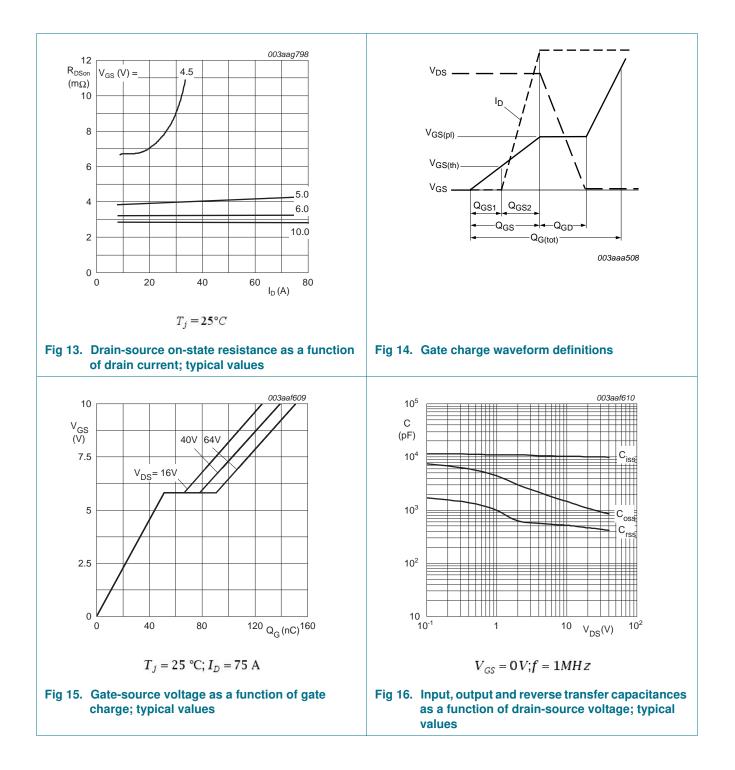
[1] Measured 3 mm from package.



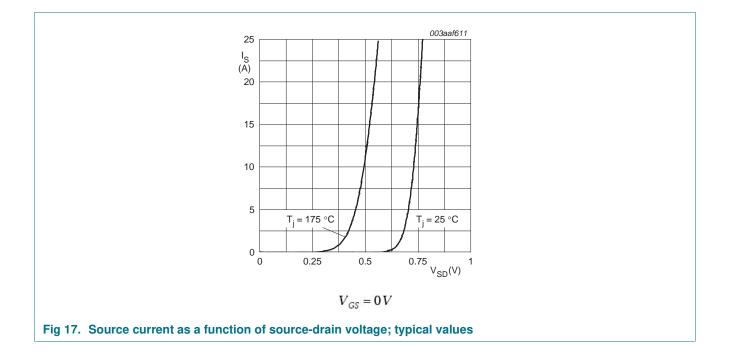
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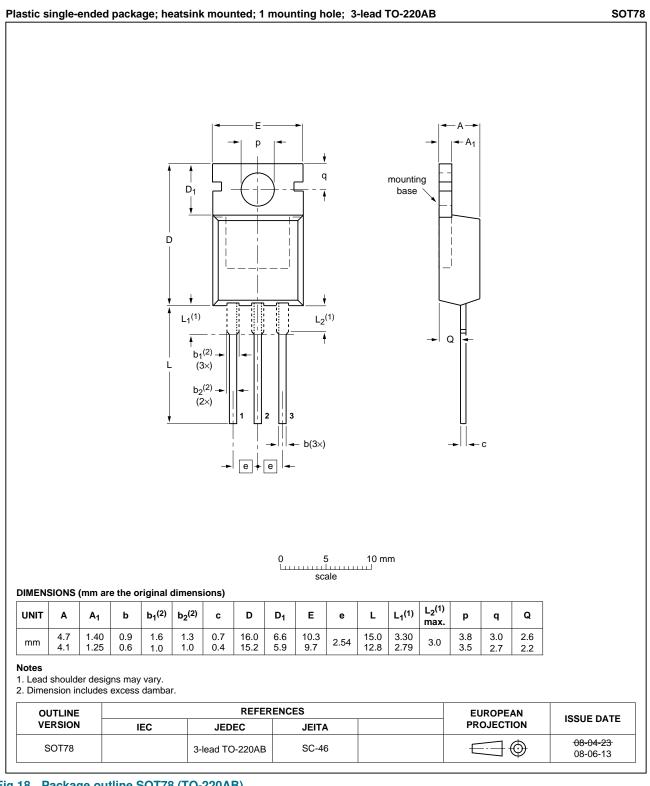


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#### N-channel 80 V, 3.3 mΩ standard level MOSFET in TO-220

#### **Package outline** 7.



#### Fig 18. Package outline SOT78 (TO-220AB)

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#### N-channel 80 V, 3.3 mΩ standard level MOSFET in TO-220

### 8. Revision history

Table 7. Revision h	Revision history						
Document ID	Release date	Data sheet status	Change notice	Supersedes			
PSMN3R3-80PS v.1	20111027	Product data sheet	-	-			

### 9. Legal information

#### 9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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